

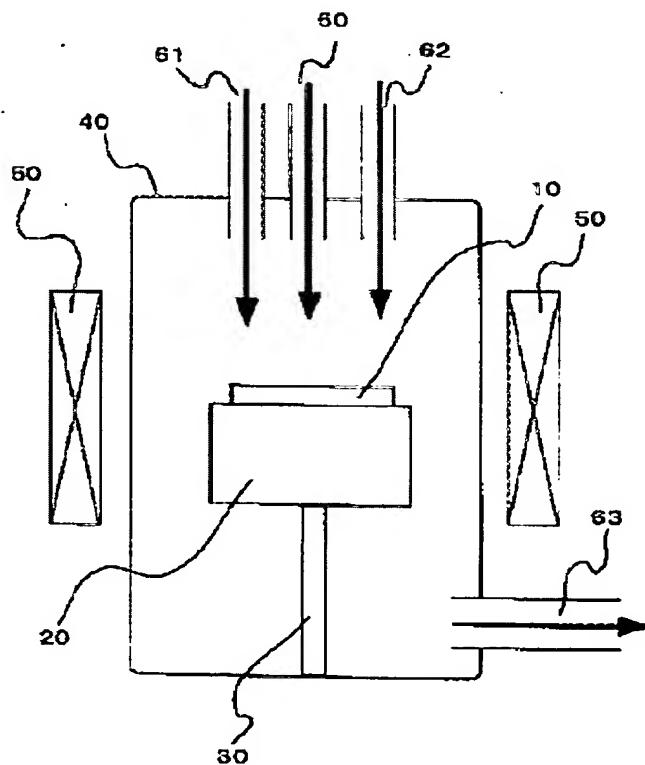
METHOD FOR TREATING NITRIDE SEMICONDUCTOR AND NITRIDE SEMICONDUCTOR AS WELL AS NITRIDE SEMICONDUCTOR ELEMENT**Publication number:** JP2003031552**Publication date:** 2003-01-31**Inventor:** TSUDA YUZO**Applicant:** SHARP KK**Classification:**

- **international:** *H01L21/302; H01L21/306; H01L21/338; H01L29/778; H01L29/812; H01L33/00; H01S5/323; H01S5/343; H01L21/02; H01L29/66; H01L33/00; H01S5/00; (IPC1-7): H01L21/306; H01L21/338; H01L29/778; H01L29/812; H01L33/00; H01S5/323*

- **europen:**

Application number: JP20010219123 20010719**Priority number(s):** JP20010219123 20010719**Report a data error here****Abstract of JP2003031552**

PROBLEM TO BE SOLVED: To improve surface morphology of a nitride semiconductor or its polishing damage. **SOLUTION:** A method for treating the nitride semiconductor comprises a step of heating the nitride semiconductor, and a step of introducing chlorine gas, an atmospheric gas and ammonia gas.



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